PDFN5×6 N
N-Channel MOSFET in a PDFN5×6 Plastic Package.

V_{DS}(V)=30 V I_D=95A
$R_{DS(ON)}$@10V≤3.6mΩ(Typ.3.5mR)
$R_{DS(ON)}$@4.5V≤6.5mΩ(Typ.5.0mR)
HF Product.

MB/NB/UMPC/VGA Buck -
Battery Management,High Frequency Point-of-

/ Absolute Maximum Ratings(T_a=25)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Continuous Drain Current		I_D	95	A
Pulsed Drain Current		I_{DM}	175	A
Gate-Source Voltage		V_{GS}	± 20	V
Power Dissipation		P_D(T_c=25)	55	W
Avalanche energy(L=0.5mH)		E_{AS}	281	mJ
Avalanche Current(L=0.5mH)		I_{AS}	26.5	A
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	
Maximum Junction-to-Ambient	t ≤ 10s	$R_{\theta JA}$	25	/ W
	Steady-State		55	
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	2.3	

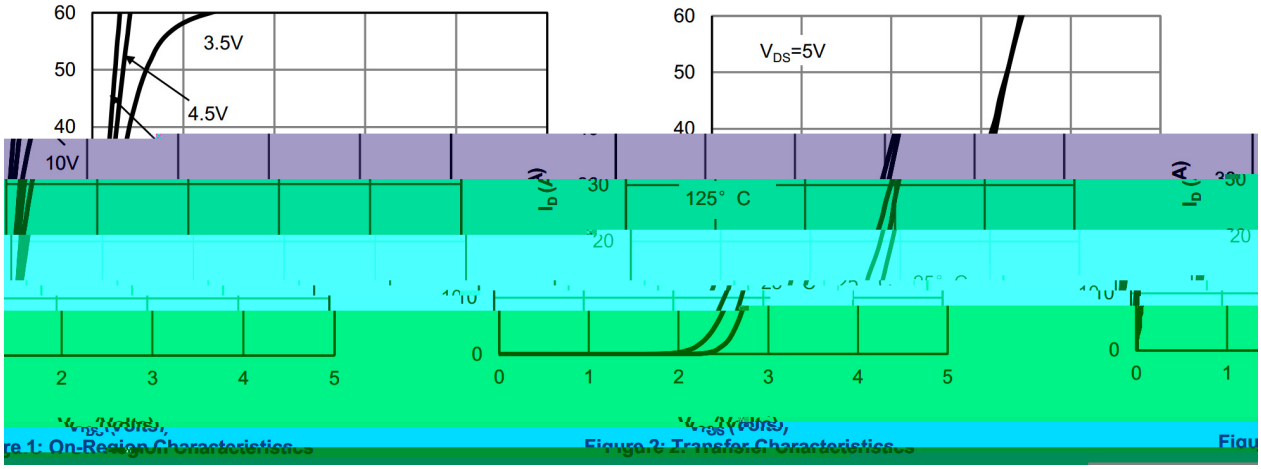
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250uA, V_{GS}=0V	30	33		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1.0	uA
Gate-Body leakage current	I_{GSS}	V_{DS}=0V, V_{GS}= ±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1	1.7	3.0	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A		3.5	3.6	mΩ
		V_{GS}=4.5V, I_D=10A		5.0	6.5	
Diode Forward Voltage	V_{SD}	I_S=1A, V_{GS}=0V			1.4	V
Input Capacitance	C_{iss}	V_{DS}=25V V_{GS}=0V f=1.0MHz		2200		pF
Output Capacitance	C_{oss}			145		
Reverse Transfer Capacitance	C_{rss}			210		
Gate resistance	R_g	V_{GS}=0V V_{DS}=0V f=1MHz		2.0		Ω

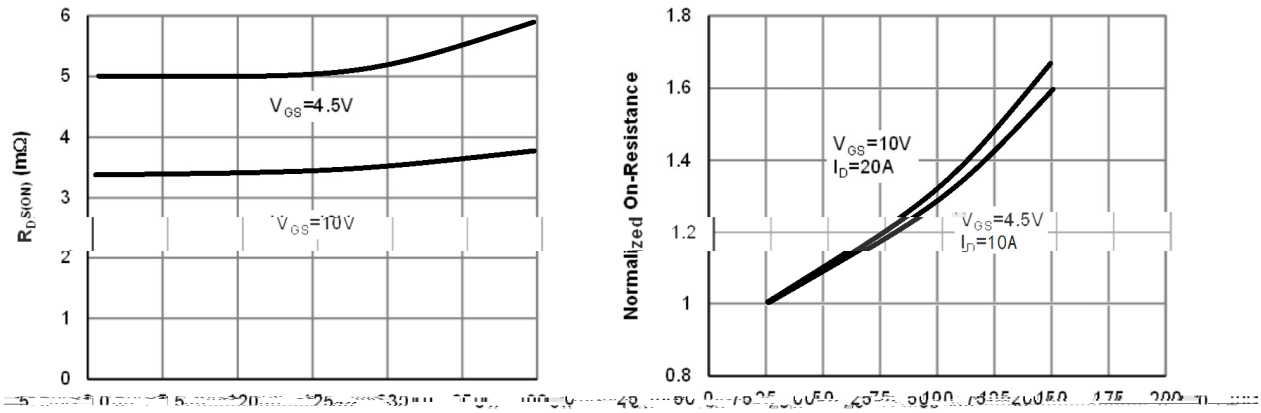
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	$Q_{g(10V)}$	V_{GS}=10V V_{DS}=15V I_D=20A		32		nC
Total Gate Charge	$Q_{g(4.5V)}$			15		
Gate Source Charge	Q_{gs}			5.2		
Gate Drain Charge	Q_{gd}			6.5		
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V V_{DS}=15V R_L=0.75Ω R_{GEN}=3Ω		8.5		ns
Turn-On Rise Time	t_r			4.2		
Turn-Off Delay Time	$t_{d(off)}$			30		
Turn-Off Fall Time	t_f			5.7		

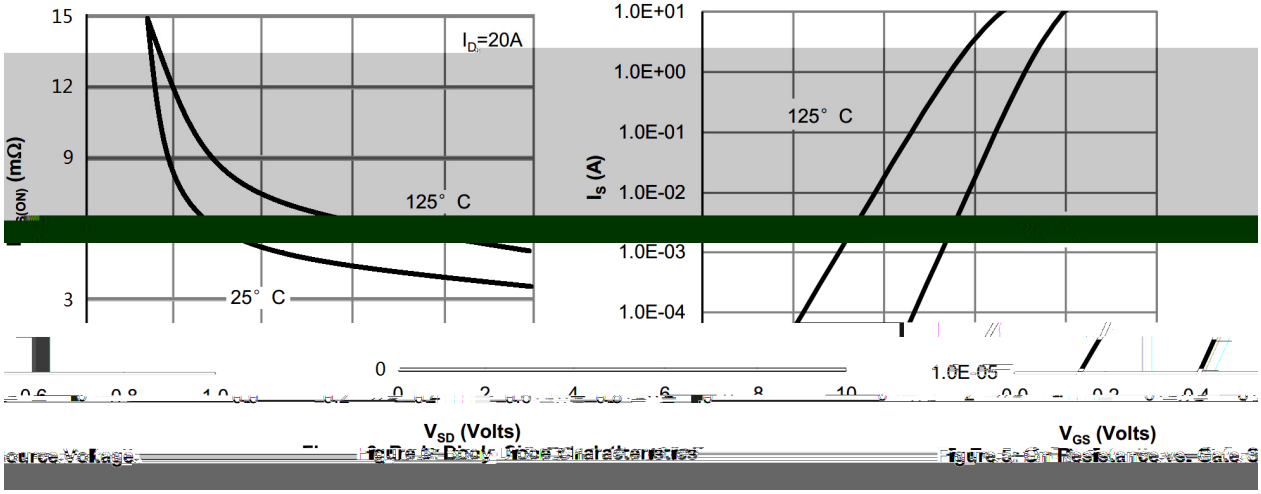
/ Electrical Characteristic Curve



re 1: On-Region Characteristics Figure 2: Transfer Characteristics Figu



emperature (°C) I_D (A) T
n-Resistance vs. Junction Figure 3: On-Resistance vs. Drain Current and Figure 4: O
Temperature Gate Voltage



ource Voltage Figure 5: Diode Forward Characteristics Figure 6: On-Resistance vs. Gate S

/ Electrical Characteristic Curve

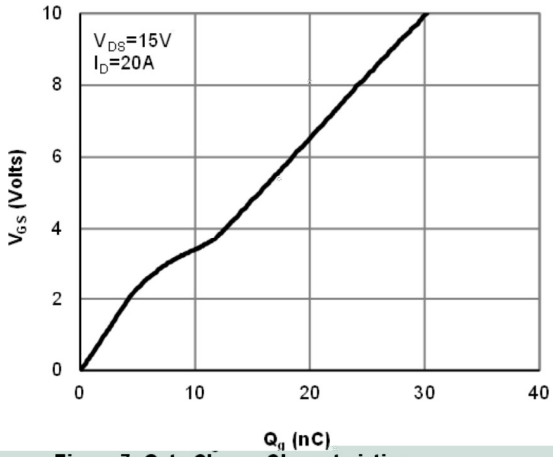


Figure 7: Gate-Charge Characteristics

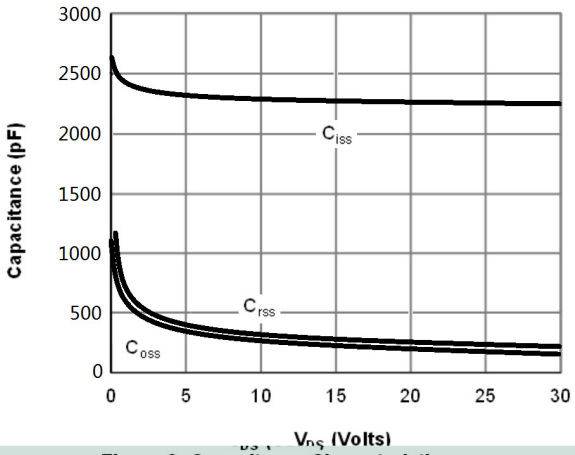


Figure 8: Capacitance Characteristics

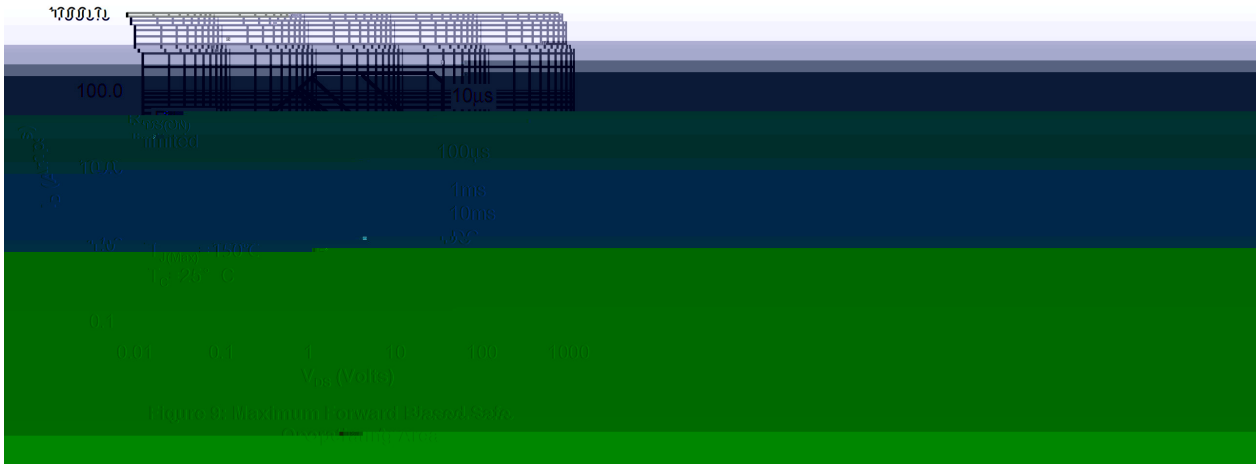


Figure 9: Maximum Forward Biased Safe

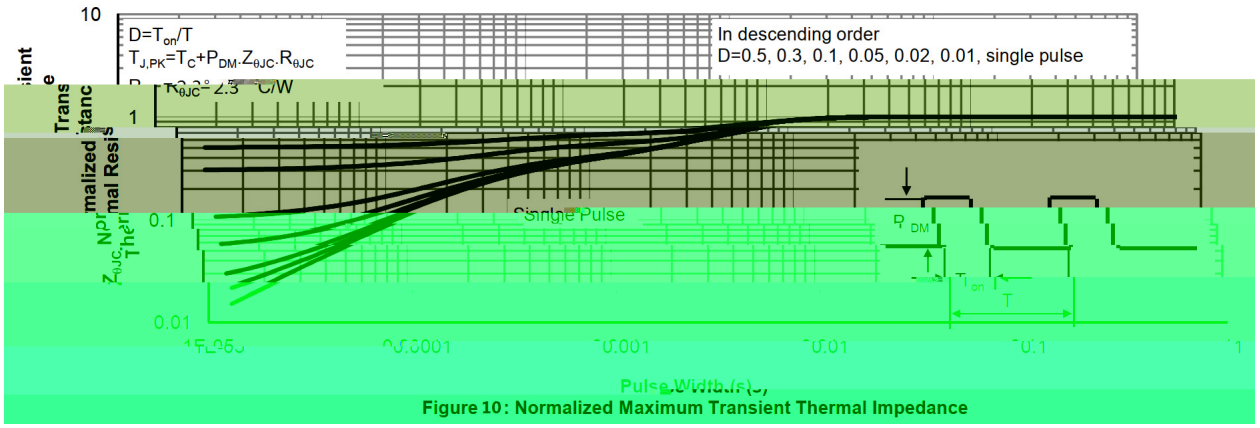
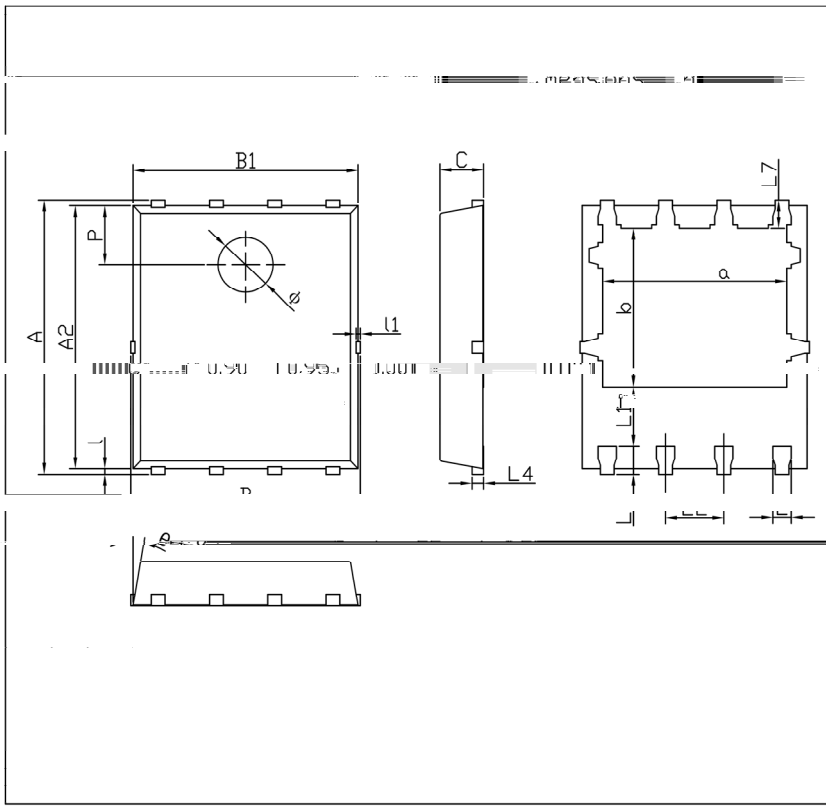


Figure 10: Normalized Maximum Transient Thermal Impedance

/ Package Dimensions

PDFN5X6

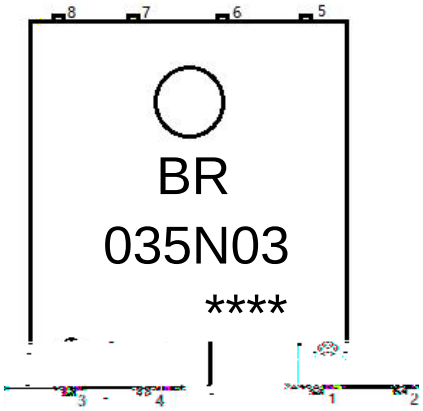
Unit:mm



Dimensions In Millimeters			
Symbol	MIN	TYP	MAX
A	5.90	6.00	6.10
a	3.91	4.01	4.11
A2	5.70	5.75	5.80
B	4.90	5.00	5.10
b	3.375	3.475	3.575
B1	4.80	4.90	5.00
C	0.30	0.40	0.50
l	0.06	0.13	0.20
L1	1.10	–	–
L2	1.17	1.27	1.37
L4	0.21	0.26	0.34
L6	0.51	0.61	0.71
L7	0.51	0.61	0.71
P	1.15	1.30	1.45
θ	8°	10°	12°
Φ	1.10	1.20	1.30

Rev.01 202209

/ Marking Instructions



BR

035N03

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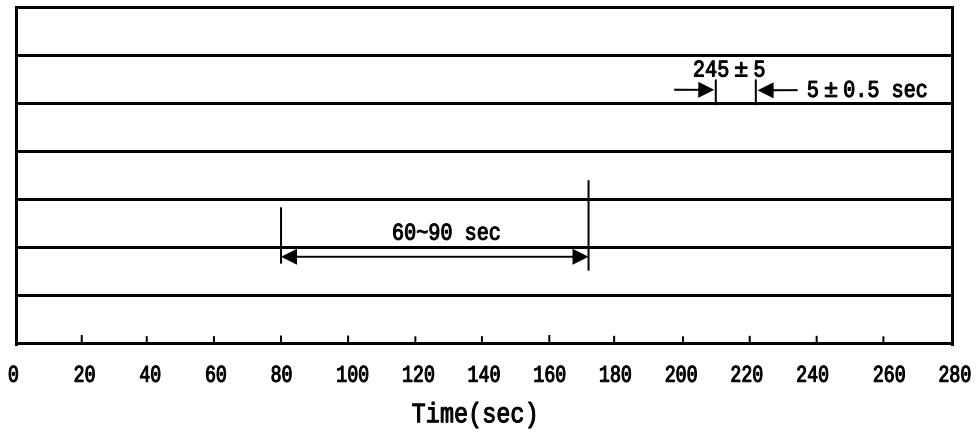
Note

BR	Company Code
035N03	Product Type Code
****:	Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



			Note:
1	150 180	60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5	5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3	2 10 /sec.		3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units					Dimension		(unit mm³)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
PDFN5×6	5,000	2	10,000	6	60,000	13''×12	360×360×50	380×335×366

/ Notices